



DMN30H4D0LFDE

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Ι _D T _A = +25°C
300V	4Ω @ V _{GS} = 10V	0.55A
	4Ω @ V _{GS} = 4.5V	0.55A
	6Ω @ V _{GS} = 2.7V	0.44A

Description

This new generation MOSFET has been designed to minimize the onstate resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

Features

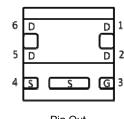
- 0.6mm profile ideal for low profile applications
- PCB footprint of 4mm²
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

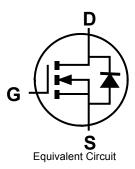
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.0065 grams (approximate)



Bottom View



Pin Out Bottom View



Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per reel
DMN30H4D0LFDE-7	Standard	U-DFN2020-6	3,000
DMN30H4D0LFDE-13	Standard	U-DFN2020-6	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2H = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013)

M = Month (ex	x: 9 = September)

Date Code Key												
Year	2013	3	2014		2015	20	16	2017		2018	2	2019
Code	A		В		С	[)	E		F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	300	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10VSteady State T_A = +25°C T_A = +70°C			ID	0.55 0.43	А
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)	I _{DM}	2	А		
Maximum Body Diode Continuous Current (Note 6)			Is	2	А

Thermal Characteristics

Characteristic	Symbol	Value	Units		
Total Power Dissipation	(Note 5)	D	0.63	W	
	(Note 6)	PD	1.98	vv	
Thermal Resistance, Junction to Ambient	(Note 5)	D	189		
Thermal Resistance, Junction to Amblent	(Note 6)	$R_{ extsf{ heta}JA}$	61	°C/W	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	9.3		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	300	_		V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	V _{DS} = 240V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1	1.7	2.8	V	V_{DS} = V_{GS} , I_D = 250 μ A	
			2.3	4		V _{GS} = 10V, I _D = 0.3A	
Static Drain-Source On-Resistance	R _{DS(ON)}		2.3	4	Ω	V _{GS} = 4.5V, I _D = 0.2A	
			2.4	6		V_{GS} = 2.7V, I_D = 0.1A	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 0.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		187.3			V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		11.7		pF		
Reverse Transfer Capacitance	C _{rss}		8.7				
Total Gate Charge	Qg		7.6	_		V _{DS} = 192V, V _{GS} = 10V,	
Gate-Source Charge	Q _{gs}		0.5	_	nC		
Gate-Drain Charge	Q _{gd}		3.3]	I _D = 0.5A	
Turn-On Delay Time	t _{D(on)}		4.9				
Turn-On Rise Time	tr		4.7			V _{DS} = 60V, R _L =200Ω	
Turn-Off Delay Time	t _{D(off)}		25.8		nS	V_{GS} = 10V, R_G = 25 Ω	
Turn-Off Fall Time	t _f		17.5]		

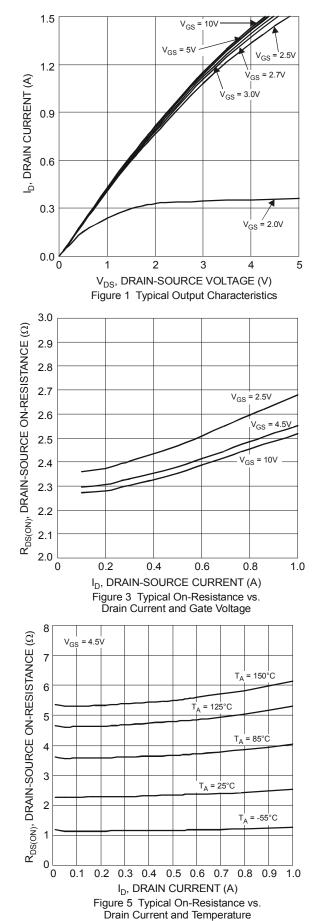
Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

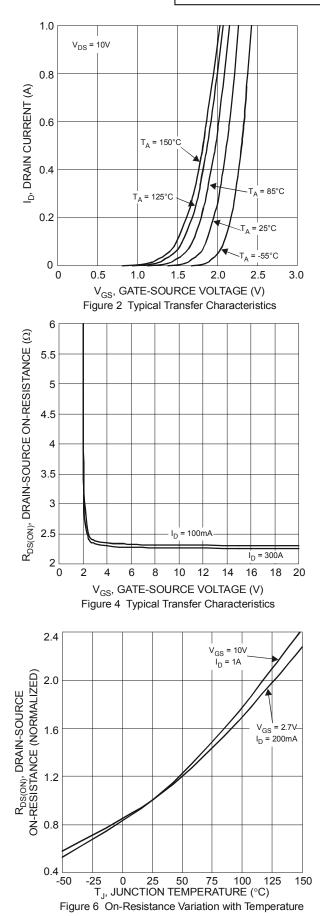
Device mounted on FR-4 substrate PC board, with minimum economic economic part layout, single sided.
Device mounted on FR-4 substrate PC board, 2z copper, with thermal bias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect
Guaranteed by design. Not subject to production testing



NEW PRODUCT

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DMN30H4D0LFDE Document number: DS36380 Rev. 4 - 2



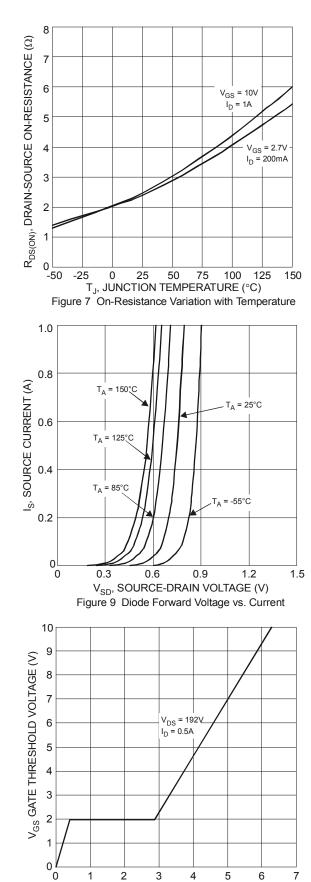
NEW PRODUCT

 $\rm C_{oss}$

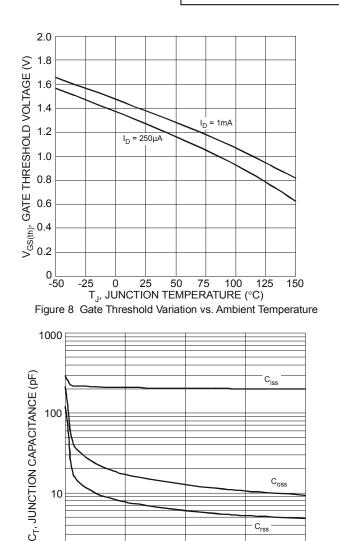
40

C_{rss}

30



Q_g, TOTAL GATE CHARGE (nC) Figure 11 Gate Charge



10

1

0

f = 1MHz

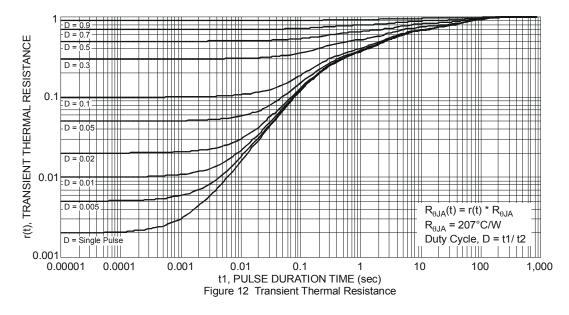
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20

 $V_{\text{DS}},$ DRAIN-SOURCE VOLTAGE (V) Figure 10 Typical Junction Capacitance

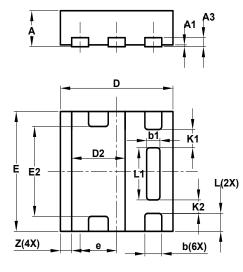


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Package Outline Dimensions

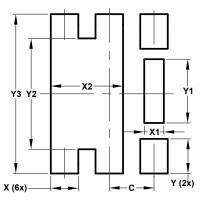
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	U-DFN2020-6 Type E								
Dim	Min Max Typ								
Α	0.57	0.63	0.60						
A1	0	0.05	0.03						
A3	_	_	0.15						
b	0.25	0.35	0.30						
b1	0.185	0.285	0.235						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
ш	1.95	2.05	2.00						
E2	1.40	1.60	1.50						
e			0.65						
L	0.25	0.35	0.30						
L1	0.82	0.92	0.87						
K1	_		0.305						
K2	_		0.225						
Z	_		0.20						
All	Dimens	ions in r	nm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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